

P-Channel Trench Power MOSFET

General Description

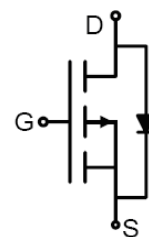
The HM2301B uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as $-2.5V$. This device is suitable for use as a battery protection or in other switching application.

Features

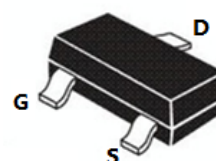
- $V_{DS} = -20V, I_D = -2.5A$
 $R_{DS(ON)} < 160m\Omega @ V_{GS} = -4.5V$
 $R_{DS(ON)} < 230m\Omega @ V_{GS} = -2.5V$
- High Power and current handling capability
- Lead free product is acquired
- Surface Mount Package

Application

- Battery protection
- Load switch
- Power management



Schematic Diagram



SOT-23 top view

Package Marking and Ordering Information

| Device Marking | Device | Device Package | Reel Size | Tape width | Quantity |
|----------------|---------|----------------|-----------|------------|-----------|
| A1SHB | HM2301B | SOT-23 | Ø180mm | 8mm | 3000units |

Table 1. Absolute Maximum Ratings ($T_A=25^\circ C$)

| Symbol | Parameter | Value | Unit |
|------------------|---|------------|------------|
| V_{DS} | Drain-Source Voltage ($V_{GS}=0V$) | -20 | V |
| V_{GS} | Gate-Source Voltage ($V_{DS}=0V$) | ± 12 | V |
| I_D | Drain Current-Continuous | -2.5 | A |
| $I_{DM (pluse)}$ | Drain Current-Continuous@ Current-Pulsed (Note 1) | -10 | A |
| P_D | Maximum Power Dissipation | 1 | W |
| T_J, T_{STG} | Operating Junction and Storage Temperature Range | -55 To 150 | $^\circ C$ |

Notes 1.Repetitive Rating: Pulse width limited by maximum junction temperature

Table 2. Thermal Characteristic

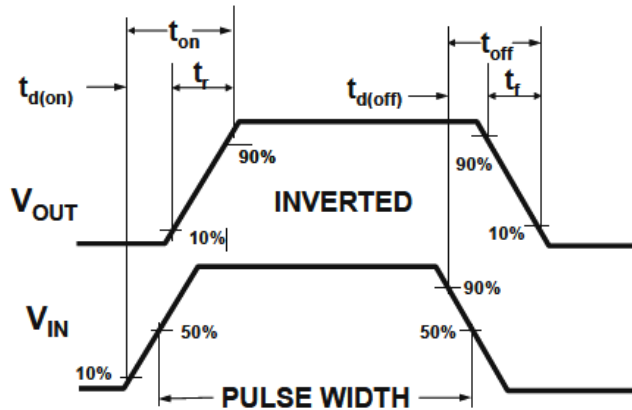
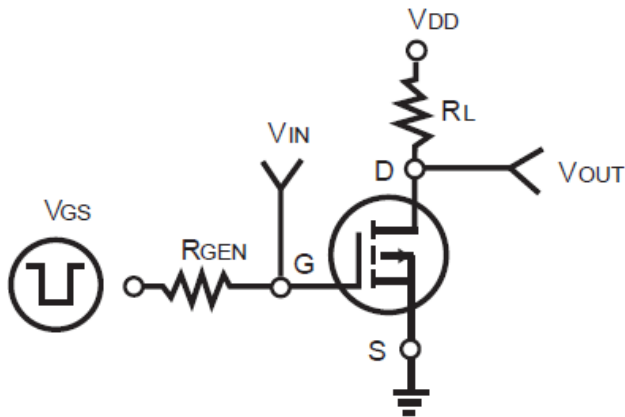
| Symbol | Parameter | Value | Unit |
|-----------------|---|-------|--------------|
| $R_{\theta JA}$ | Thermal Resistance, Junction-to-Ambient | 125 | $^\circ C/W$ |

Table 3. Electrical Characteristics (T_A=25°C unless otherwise noted)

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|---|--|--|------|------|------|------|
| On/Off States | | | | | | |
| B _V DSS | Drain-Source Breakdown Voltage | V _{GS} =0V, I _D =-250μA | -20 | -23 | | V |
| I _{DSS} | Zero Gate Voltage Drain Current | V _{DS} =-20V, V _{GS} =0V | | | -1 | μA |
| I _{GSS} | Gate-Body Leakage Current | V _{GS} =±12V, V _{DS} =0V | | | ±100 | nA |
| V _{GS(th)} | Gate Threshold Voltage | V _{DS} =V _{GS} , I _D =-250μA | -0.4 | -0.7 | -1 | V |
| g _{FS} | Forward Transconductance | V _{DS} =-5V, I _D =-2A | 4 | | | S |
| R _{DS(ON)} | Drain-Source On-State Resistance | V _{GS} =-4.5V, I _D =-2.5A | | 118 | 160 | mΩ |
| | | V _{GS} =-2.5V, I _D =-2A | | 175 | 230 | mΩ |
| | | V _{GS} =-1.8V, I _D =-2A | | 310 | 390 | mΩ |
| Dynamic Characteristics | | | | | | |
| C _{ISS} | Input Capacitance | V _{DS} =-10V, V _{GS} =0V, f=1.0MHz | | 290 | | pF |
| C _{OSS} | Output Capacitance | | | 55 | | pF |
| C _{RSS} | Reverse Transfer Capacitance | | | 29 | | pF |
| Switching Times | | | | | | |
| t _{d(on)} | Turn-on Delay Time | V _{DD} =-10V, I _D =-1A, R _L =2.8Ω V _{GS} =-4.5V, R _G =6Ω | | 8 | | nS |
| t _r | Turn-on Rise Time | | | 13 | | nS |
| t _{d(off)} | Turn-Off Delay Time | | | 13 | | nS |
| t _f | Turn-Off Fall Time | | | 18 | | nS |
| Q _g | Total Gate Charge | V _{DS} =-10V, I _D =-2.5A, V _{GS} =-4.5V | | 3 | | nC |
| Q _{gs} | Gate-Source Charge | | | 0.7 | | nC |
| Q _{gd} | Gate-Drain Charge | | | 0.8 | | nC |
| Source-Drain Diode Characteristics | | | | | | |
| I _{SD} | Source-Drain Current(Body Diode) | | | | -2.5 | A |
| V _{SD} | Forward on Voltage ^(Note 1) | V _{GS} =0V, I _S =-2.5A | | | -1.2 | V |

Notes 1. Repetitive Rating: Pulse width limited by maximum junction temperature.

Switch Time Test Circuit and Switching Waveforms:



TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS (Curves)

Figure1. Power Dissipation

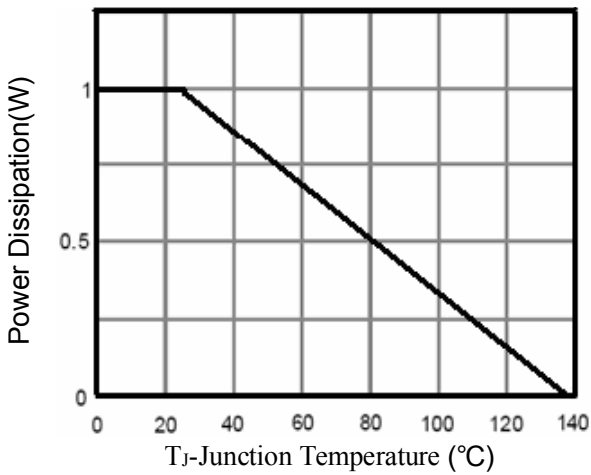


Figure2. Drain Current

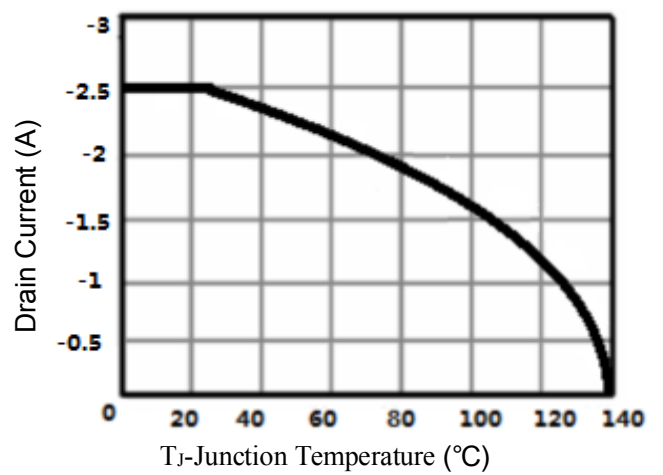


Figure3. Output Characteristics

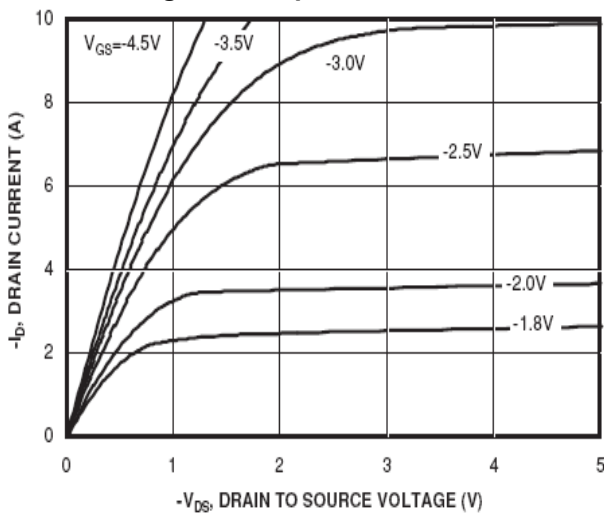


Figure4. Transfer Characteristics

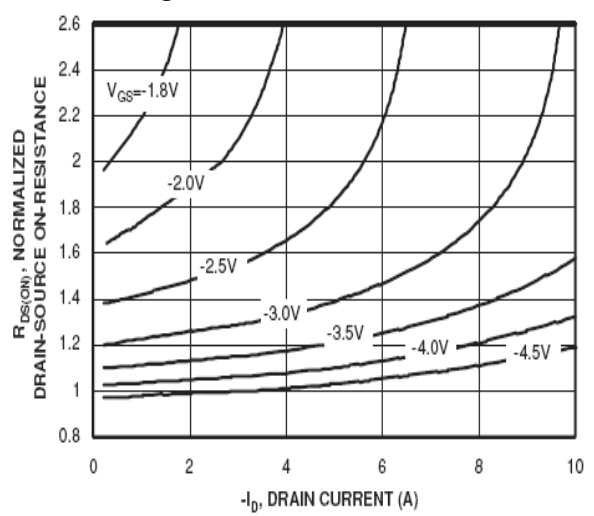


Figure5. Capacitance

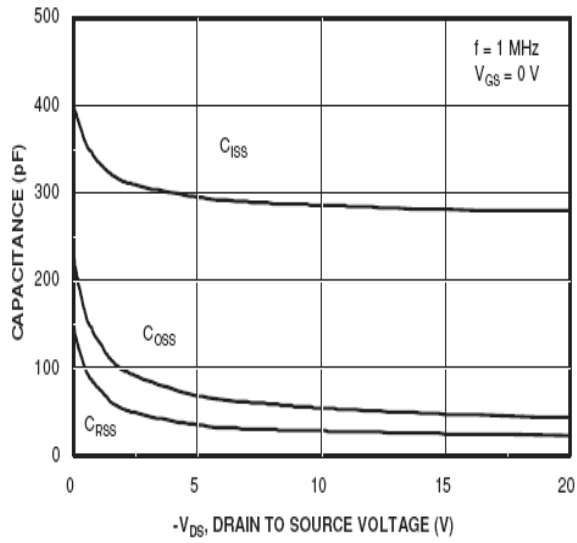


Figure6. $R_{DS(ON)}$ vs Junction Temperature

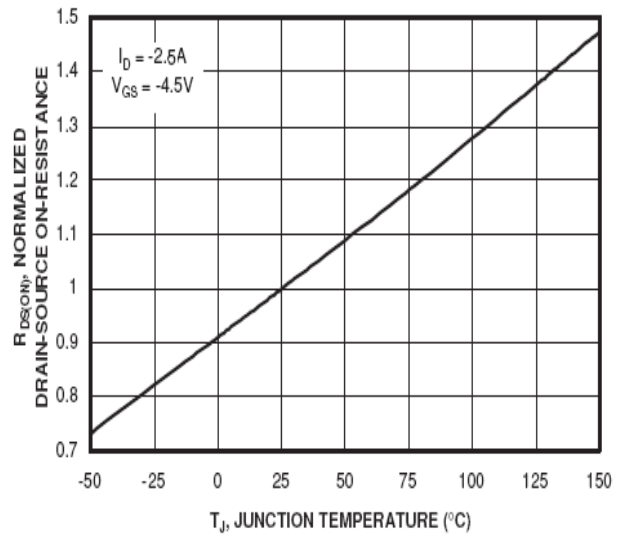


Figure7. Max BV_{DSS} vs Junction Temperature

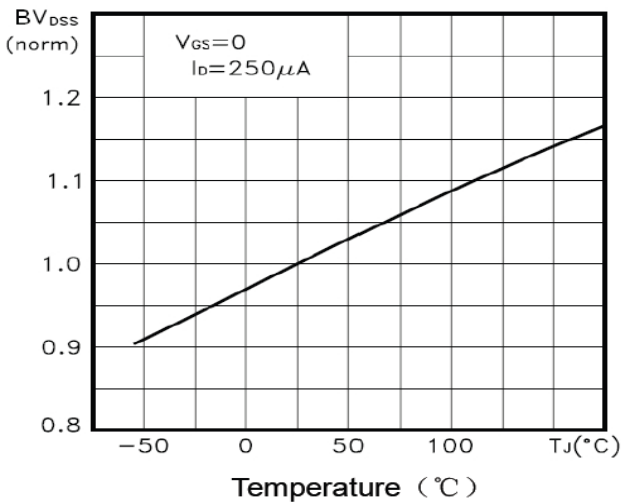


Figure8. $V_{GS(th)}$ vs Junction Temperature

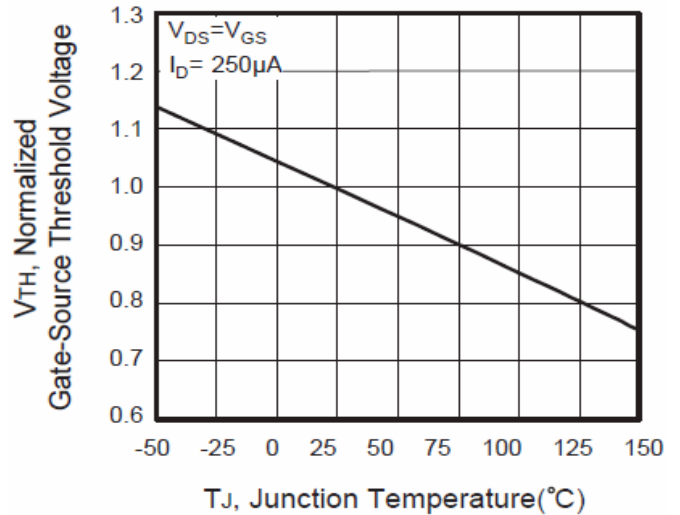


Figure9. Gate Charge Waveforms

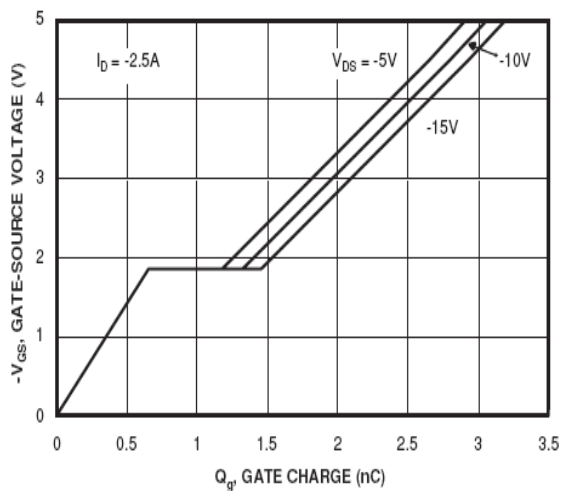


Figure10. Maximum Safe Operating Area

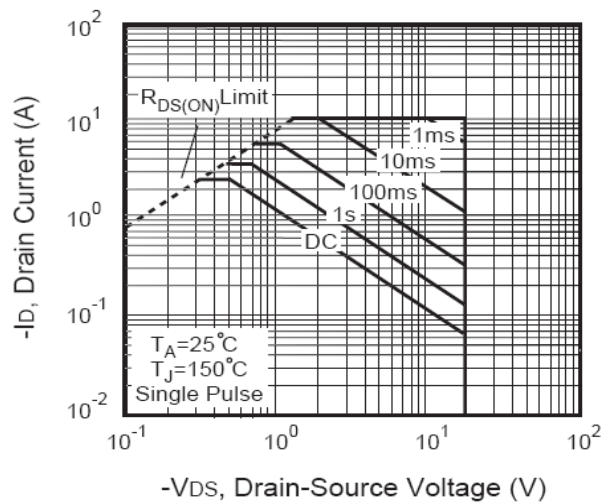
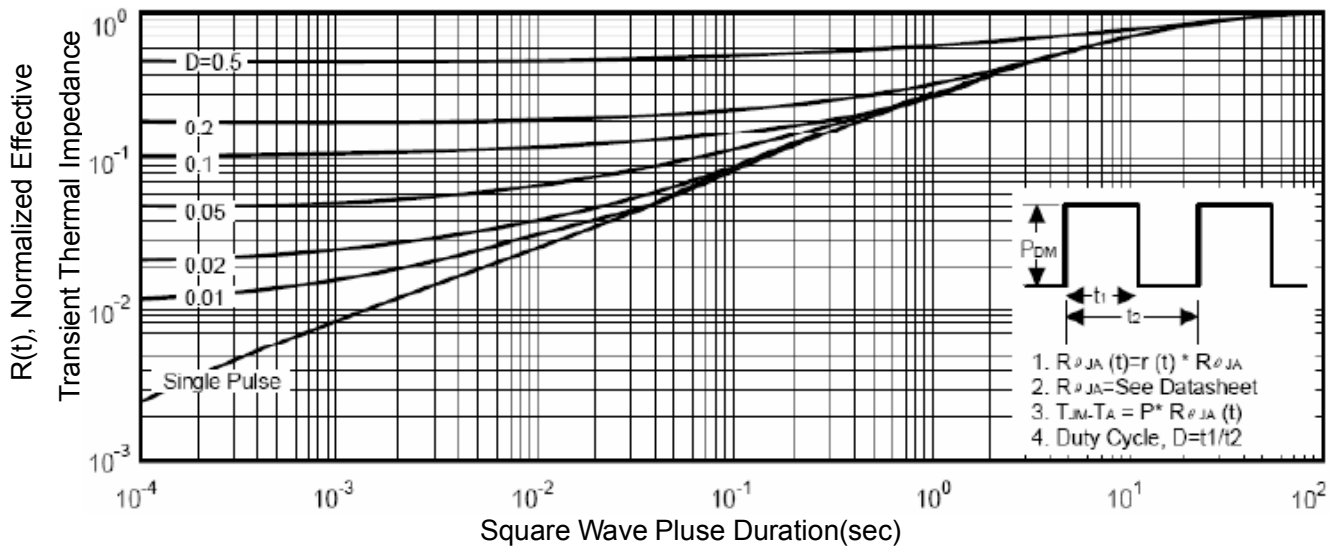
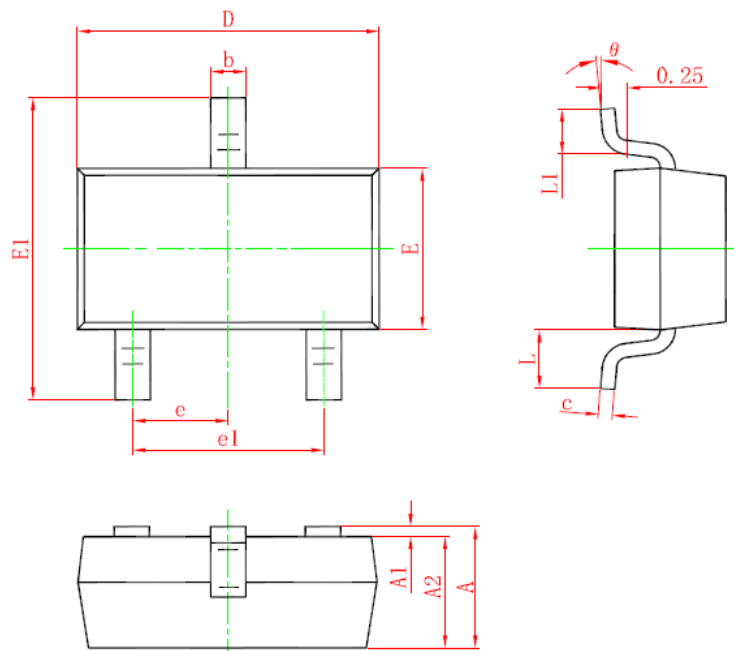


Figure11. Normalized Maximum Transient Thermal Impedance



SOT-23 Package Information



| Symbol | Dimensions In Millimeters | | Dimensions In Inches | |
|--------|---------------------------|-------|----------------------|-------|
| | Min. | Max. | Min. | Max. |
| A | 0.900 | 1.150 | 0.035 | 0.045 |
| A1 | 0.000 | 0.100 | 0.000 | 0.004 |
| A2 | 0.900 | 1.050 | 0.035 | 0.041 |
| b | 0.300 | 0.500 | 0.012 | 0.020 |
| c | 0.080 | 0.150 | 0.003 | 0.006 |
| D | 2.800 | 3.000 | 0.110 | 0.118 |
| E | 1.200 | 1.400 | 0.047 | 0.055 |
| E1 | 2.250 | 2.550 | 0.089 | 0.100 |
| e | 0.950 TYP. | | 0.037 TYP. | |
| e1 | 1.800 | 2.000 | 0.071 | 0.079 |
| L | 0.550 REF. | | 0.022 REF. | |
| L1 | 0.300 | 0.500 | 0.012 | 0.020 |
| θ | 0° | 8° | 0° | 8° |